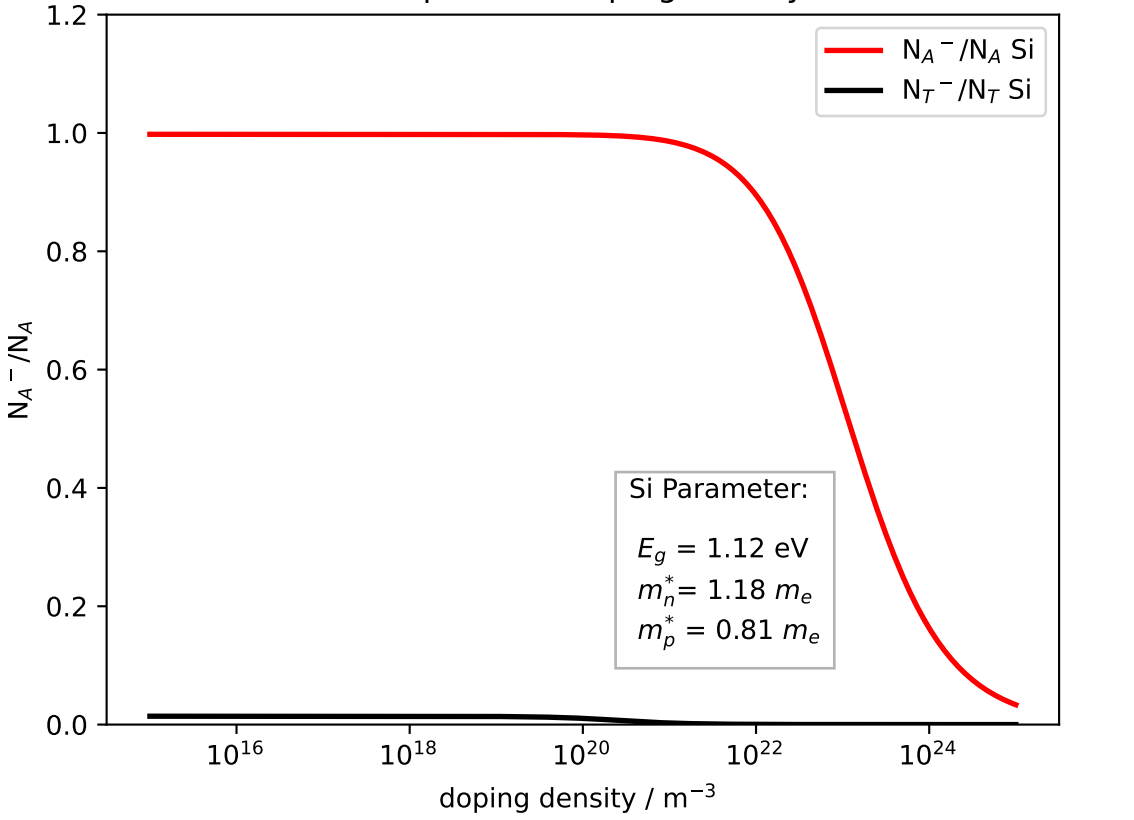
Number of Ionized Dopants vs doping density for Si at $T = 300K$
N_A^-/N_A Si
N_T^-/N_T Si
Si Parameter:
E_g = 1.12 eV
m_n^*= 1.18 m_e
m_p^* = 0.81 m_e
N_A^-/N_A
doping density / m^{-3}
1.2
1.0
0.8
0.6
0.4
0.2
0.0
10^{16}
10^{18}
10^{20}
10^{22}
10^{24}